ABSTRACT

Provided herein is a memory device and a method of manufacturing the memory device. The method of manufacturing a memory device includes forming a stacked body including first and second material layers on a lower structure, forming first openings passing through the stacked body, filling the first openings with preliminary contact plugs, respectively, forming, on the stacked body, a stepped structure including steps respectively corresponding to the preliminary contact plugs, forming second openings passing through respective steps of the stepped structure and open at least portions of the first openings, respectively, at different depths, exposing side surfaces of the second material layers by removing respective portions of the preliminary contact plugs adjacent to respective first sides of the first openings through the second openings, and forming the stacked body having a reverse step structure by removing exposed portions of the second material layers.

FIG. 3A